INTEGRATED CIRCUITS



Product specification Supersedes data of March 1995 File under Integrated Circuits, IC02 1996 Aug 16



TDA5632; TDA5633

FEATURES

- · Balanced mixer with a common emitter input for band A
- 2-pin oscillator for band A
- Balanced mixer with a common base input for band C
- 4-pin oscillator for band C
- · Local oscillator buffer output for external prescaler
- SAW filter preamplifier with a low output impedance to drive a 75 Ω load
- · Band gap voltage stabilizer for oscillator stability
- Electronic band switch
- External IF filter connected between the mixer output and the IF amplifier input.

APPLICATIONS

- Cable tuners for TV and VTR; switched concept for VHF
- Recommended RF bands for Europe: 48.25 to 105.25 MHz, 112.25 to 294.25 MHz and 471.25 to 855.25 MHz
- Recommended RF bands for the USA: 55.25 to 133.25 MHz, 139.25 to 361.25 MHz and 367.25 to 801.25 MHz.

DESCRIPTION

The TDA5632 and TDA5633 are monolithic integrated circuits that perform VHF and UHF mixer/oscillator functions in TV and VCR cable tuners. With correct oscillator application and by using a switchable inductor to split the VHF band into two sub-bands, the full VHF/UHF TV bands can be covered. These low-power mixers/oscillators require a power supply of 9 V and are available in a very small package.

The devices provide the designer with the capability to design an economical and physically small cable tuner.

The tuner development time can be drastically reduced by using this device.

Frequency bands are determined by the external tank circuit. They can be adapted to various standards.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------|-----------------------------------|---------------------------|-------|------|-------|------|
| VP | supply voltage | | _ | 9.0 | _ | V |
| IP | supply current | | _ | 40 | _ | mA |
| f _{RF} | frequency range (picture carrier) | RF input; band A; note 1 | 57.5 | - | 357.5 | MHz |
| | | RF input; band C; note 1 | 469.5 | - | 887.5 | MHz |
| G _v | voltage gain | band A (75 Ω load) | - | 19 | - | dB |
| | | band C (75 Ω load) | - | 30 | - | dB |
| NF | noise figure | band A (75 Ω load) | _ | 10 | _ | dB |
| | | band C (75 Ω load) | _ | 9.5 | _ | dB |
| Vo | output voltage to obtain 1% cross | band A (75 Ω load) | - | 110 | - | dBµV |
| | modulation in channel | band C (75 Ω load) | - | 110 | _ | dBµV |

QUICK REFERENCE DATA

Note

- 1. The limits are related to the tank circuits used in Fig.10 and the intermediate frequency. Frequency bands may be adjusted by the choice of external components. Another UHF frequency range is available by modifying the tank circuit. The modification enables the following frequency range:
 - a) RF frequencies from 361.25 to 801.25 MHz (picture carrier).
 - b) Oscillator frequencies from 407 to 847 MHz. For this UHF range, L4 = 3 turns (diameter = 3.5 mm).

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ORDERING INFORMATION

| TYPE | | PACKAGE | | |
|----------|--------|---|----------|--|
| NUMBER | NAME | NAME DESCRIPTION VER | | |
| TDA5632T | SO20 | plastic small outline package; 20 leads; body width 7.5 mm | SOT163-1 | |
| TDA5632M | SSOP20 | plastic shrink small outline package; 20 leads; body width 4.4 mm | SOT266-1 | |
| TDA5633T | SO20 | plastic small outline package; 20 leads; body width 7.5 mm | SOT163-1 | |
| TDA5633M | SSOP20 | plastic shrink small outline package; 20 leads; body width 4.4 mm | SOT266-1 | |

BLOCK DIAGRAM



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PINNING

| SYMBOL | | IN | DECODIDITION |
|----------------|---------|---------|--------------------------------------|
| STMBOL | TDA5632 | TDA5633 | DESCRIPTION |
| AOSCIB | 1 | 20 | band A oscillator input base |
| GND | 2 | 19 | ground (0 V) |
| AOSCOC | 3 | 18 | band A oscillator output collector |
| COSCIB1 | 4 | 17 | band C oscillator input base 1 |
| COSCOC1 | 5 | 16 | band C oscillator output collector 1 |
| COSCOC2 | 6 | 15 | band C oscillator output collector 2 |
| COSCIB2 | 7 | 14 | band C oscillator input base 2 |
| BS | 8 | 13 | band switch input |
| n.c. | 9 | 12 | not connected |
| IFOUT | 10 | 11 | IF amplifier output |
| IFIN1 | 11 | 10 | IF amplifier input 1 |
| IFIN2 | 12 | 9 | IF amplifier input 2 |
| V _P | 13 | 8 | supply voltage |
| LOOUT1 | 14 | 7 | local oscillator amplifier output 1 |
| LOOUT2 | 15 | 6 | local oscillator amplifier output 2 |
| RFGND | 16 | 5 | ground for RF inputs |
| CIN1 | 17 | 4 | band C input 1 |
| CIN2 | 18 | 3 | band C input 2 |
| AIN1 | 19 | 2 | band A input 1 |
| AIN2 | 20 | 1 | band A input 2 |





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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | MIN. | MAX. | UNIT |
|------------------|---|------|-------|------|
| V _P | supply voltage | -0.3 | +10.5 | V |
| V _{SW} | switching voltage | 0 | 10.5 | V |
| I _O | output current of each pin referenced to ground | - | -10 | mA |
| t _{sc} | maximum short-circuit time (all pins) | - | 10 | S |
| T _{stg} | IC storage temperature | -55 | +150 | °C |
| T _{amb} | operating ambient temperature | -20 | +85 | °C |
| Tj | junction temperature | _ | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | VALUE | UNIT |
|---------------------|---|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient in free air | | |
| | SOT163-1 | 80 | K/W |
| | SOT266-1 | 120 | K/W |

HANDLING

Human body model: the IC withstands 2000 V in accordance with the "UZW-B0/FQ-A302"; specification equivalent to the "MIL-STD-883C, category B"; $R = 1.5 k\Omega$; C = 100 pF.

Machine model: the IC withstands 200 V in accordance with the "UZW-B0/FQ-B302" (date of issue: Nov 6th, 1990); $R = 0 \Omega$; C = 200 pF.

IF AMPLIFIER CHARACTERISTICS

 $V_P = 9 V$; $T_{amb} = 25 \circ C$; measured at 43.5 MHz; measured in circuit of Fig.10; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------|-------------------------------|--|------|-------|------|------|
| S ₂₂ | output reflection coefficient | f _{IF} = 43.5 MHz; see Fig.9 | - | -13.1 | - | dB |
| | | f _{IF} = 43.5 MHz; see Fig.9 | - | 2.9 | - | deg |
| | | f _{IF} = 58.75 MHz; see Fig.9 | - | -13.1 | _ | dB |
| | | f _{IF} = 58.75 MHz; see Fig.9 | - | 2.2 | - | deg |
| Zo | output impedance | f _{IF} = 43.5 MHz; see Fig.9 | - | 78.4 | - | Ω |
| | | f _{IF} = 43.5 MHz; see Fig.9 | - | 1.8 | - | Ω |
| | | f _{IF} = 58.75 MHz; see Fig.9 | - | 78.4 | _ | Ω |
| | | f _{IF} = 58.75 MHz; see Fig.9 | - | -1.4 | _ | Ω |

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CHARACTERISTICS

 V_{P} = 9 V; T_{amb} = 25 °C; measured in circuit of Fig.10; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|---|--|------|------|-------|------|
| Supply | | | • | • | • | • |
| V _P | supply voltage | | 8.1 | 9.0 | 9.9 | V |
| I _P | supply current | | - | 40 | 48 | mA |
| V _{SW} | switching voltage | band A | 0 | - | 2.0 | V |
| | | band C | 3.0 | - | 5.0 | V |
| I _{SW} | switching current | band A | - | - | 2 | μA |
| | | band C | _ | - | 10 | μA |
| Band A m | ixer including IF amplifier | | • | | | |
| f _{RF} | frequency range | note 1 | 57.5 | - | 357.5 | MHz |
| Gv | voltage gain | f_{RF} = 57.5 MHz; R_L = 75 Ω ; see Fig.4 | 16.5 | 19 | 21.5 | dB |
| | | f_{RF} = 357.5 MHz; R _L = 75 Ω; see Fig.4 | 16.5 | 19 | 21.5 | dB |
| NF | noise figure | f_{RF} = 50 MHz; R_L = 75 Ω ; see Fig.5 | - | 7.5 | 9.5 | dB |
| | f_{RF} = 150 MHz; R_L = 75 Ω ; see Fig.5 | - | 8.5 | 10.5 | dB | |
| | f _{RF} = 300 MHz; R _L = 75 Ω | - | 10 | 12.5 | dB | |
| Vo | output voltage causing 1% | f_{RF} = 57.5 MHz; R_L = 75 Ω ; see Fig.6 | 107 | 110 | - | dBμV |
| | cross modulation in channel | f_{RF} = 357.5 MHz; R _L = 75 Ω; see Fig.6 | 107 | 110 | - | dBµV |
| Vi | input voltage causing 10 kHz pulling in channel | f_{RF} = 357.5 MHz; R_L = 75 Ω ; see note 2 | - | 91 | - | dBµV |
| g _{os} | optimum source | f_{RF} = 50 MHz; R_L = 75 Ω | - | 0.5 | - | mS |
| | conductance for noise figure | f _{RF} = 150 MHz; R _L = 75 Ω | - | 1.1 | _ | mS |
| | | f_{RF} = 300 MHz; R_L = 75 Ω | - | 1.9 | - | mS |
| gi | input conductance | f _{RF} = 57.5 MHz | - | 0.27 | _ | mS |
| | | f _{RF} = 357.5 MHz | - | 0.68 | - | mS |
| Ci | input capacitance | f_{RF} = 57.5 to 357.5 MHz; R_L = 75 Ω | - | 2 | - | pF |
| Band A os | scillator | | • | | | |
| f _{osc} | frequency range | note 3 | 101 | - | 401 | MHz |
| f _{shift} | frequency shift | $\Delta V_{P} = 10\%$; note 4 | - | - | 200 | kHz |
| f _{drift} | frequency drift | $\Delta T = 25$ °C with no compensation; NP0 capacitors; note 5 | - | - | 1200 | kHz |
| | | 5 s to 15 min after switch on; note 6 | - | - | 400 | kHz |

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| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|---|---|------------|------|-------|------|
| Band C m | ixer including IF amplifier | | - ! | 1 | 1 | 1 |
| f _{RF} | frequency range | note 1 | 469.5 | _ | 887.5 | MHz |
| G _v | voltage gain | f_{RF} = 469.50 MHz; R _L = 75 Ω; see Fig.7 | 27 | 30 | 33 | dB |
| | | f _{RF} = 887.5 MHz; R _L = 75 Ω; see Fig.7 | 27 | 30 | 33 | dB |
| NF | noise figure | f_{RF} = 469.50 MHz; R _L = 75 Ω | _ | 7.5 | 9.5 | dB |
| | (not corrected for image) | f _{RF} = 887.5 MHz; R _L = 75 Ω | _ | 9.5 | 11.5 | dB |
| Vo | output voltage causing 1% cross modulation in channel | f_{RF} = 887.5 MHz; R_L = 75 Ω ; see Fig.8 | 107 | 110 | - | dBμV |
| Zi | input impedance (R _s + L _s) | R _s ; f _{RF} = 469.50 MHz | _ | 30 | - | Ω |
| | | L _s ; f _{RF} = 887.5 MHz | _ | 12 | _ | nH |
| Vi | input voltage causing 10 kHz pulling in channel | $R_L = 75 \Omega$; note 2 | - | 82 | - | dBμV |
| Band C os | scillator | | | | | |
| f _{osc} | frequency range | note 3 | 513 | - | 931 | MHz |
| f _{shift} | frequency shift | $\Delta V_P = 10\%$; note 4 | _ | - | 500 | kHz |
| f _{drift} | frequency drift | $\Delta T = 25 \ ^{\circ}C$ with compensation; note 5 | _ | - | 900 | kHz |
| | | 5 s to 15 min after switching on; note 6 | _ | - | 400 | kHz |
| LO output | | | • | | | |
| Vo | output voltage | R _L = 50 Ω | 83 | 91 | 100 | dBμV |
| SRF | spurious signal on LO output with respect to LO output signal | $R_L = 50 \Omega$; note 7 | - | -14 | -10 | dB |
| SHD | LO signal harmonics with respect to LO signal | R _L = 50 Ω | - | -11 | -10 | dB |

Notes

- 1. The RF frequency range is defined by the oscillator frequency range and the intermediate frequency.
- 2. The input level causing 10 kHz detuning at the LO output; $f_{osc} = f_{RF} + 43.5$ MHz.
- Limits are related to the tank circuit used in Fig.10. Frequency bands may be adjusted by the choice of external components. Another UHF frequency range is available by modifying the tank circuit. The modification enables the following frequency range:
 - a) RF frequencies from 363.5 to 803.5 MHz.
 - b) Oscillator frequencies from 407 to 847 MHz. For this UHF range, L4 = 3 turns (diameter = 3.5 mm).
- 4. The frequency shift is defined as the change in oscillator frequency when the supply voltage varies from $V_P = 9$ to 8.1 V or $V_P = 9$ to 9.9 V.
- The frequency drift is defined as the change in oscillator frequency when the ambient temperature varies from T_{amb} = 25 to 0 °C or T_{amb} = 25 to 50 °C.
- 6. Switch on drift is defined as the change in oscillator frequency between 5 s and 15 min after switch on.
- 7. SRF: spurious signal on LO output with respect to LO signal:
 - a) RF voltage level = 1 V at f_{RF} = 57.5 to 225 MHz.
 - b) RF level = 2.5 dBm at f_{RF} = 225 to 357.5 MHz.
 - c) RF level = -10 dBm at f_{RF} = 469.5 to 887.5 MHz.

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Fig.5 Input circuit for minimum noise figure.









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APPLICATION INFORMATION



Application diagram component values

Table 1Capacitors (all SMD and NP0 except
C9, C11 to C14 and C30)

| NUMBER | VALUE |
|--------|---|
| C1 | 1 nF |
| C2 | 1 nF |
| C3 | 1 nF |
| C4 | 56 pF |
| C5 | 2.2 nF |
| C6 | 2 pF |
| C7 | 4 pF |
| C8 | 2.2 nF |
| C9 | 6 pF (N470) |
| C10 | 100 pF |
| C11 | 1 pF (N750) |
| C12 | 1 pF (N750) |
| C13 | 1 pF (N750) |
| C14 | 1 pF (N750) |
| C17 | 1 nF |
| C18 | 1 nF |
| C19 | 1 nF |
| C20 | 1 nF |
| C21 | 1 nF |
| C22 | 1 nF |
| C23 | 1 nF |
| C24 | 1 nF |
| C26 | 15 pF |
| C27 | 15 pF |
| C28 | 2.2 nF |
| C29 | 1 nF |
| C30 | $1 \ \mu F$ (40 V electrolytic capacitor) |

| NUMBER | VALUE |
|--------|--------|
| R1 | 10 Ω |
| R2 | 12 kΩ |
| R3 | 2.7 kΩ |
| R4 | 47 kΩ |
| R5 | 56 Ω |
| R6 | 47 kΩ |
| R7 | 22 kΩ |

| NUMBER | VALUE |
|--------|--------|
| R8 | 2.2 kΩ |
| R9 | 22 kΩ |
| R10 | 100 Ω |
| R11 | 47 kΩ |
| R12 | 47 kΩ |
| R13 | 150 Ω |
| R16 | 27 Ω |

Table 3 Diodes and coils

| NUMBER | VALUE |
|----------------------|--------------|
| Diodes | |
| D1 | BA682 |
| D2 | BB133 |
| D3 | BB134 |
| D6 | BB131 |
| D7 | BB131 |
| Coils ⁽¹⁾ | |
| L1 | 6 t (4 mm) |
| L2 | 3 t (3.5 mm) |
| L3 | 2 t (2.5 mm) |
| L4 | 3 t (2.5 mm) |

Note

1. Wire size for L1 to L4 is 0.4 mm.

Transformer (L7 = $2 \times 5 t$)

Coil type: TOKO 7 KN; material: 113 KN, screw core (03-0093), pot core (04-0026).

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INTERNAL PIN CONFIGURATION

| 0/110-01 | PIN | | | AVERAGE DC VOLTAGE (V) ⁽¹⁾ | |
|----------|--------------------------------|-------------|---|---------------------------------------|-------------------|
| SYMBOL | SYMBOL DESCRIPTION DESCRIPTION | DESCRIPTION | BAND A | BAND C | |
| AOSCIB | 1 | 20 | | 2.20 | NR ⁽²⁾ |
| AOSCOC | 3 | 18 | (1) (20) (20) (18) (18) (18) (18) (18) (18) | 3.90 | NR ⁽²⁾ |
| GND | 2 | 19 | (19) | 0 | 0 |
| COSCIB1 | 4 | 17 | | NR ⁽²⁾ | 2.35 |
| COSCOC1 | 5 | 16 | П | NR ⁽²⁾ | 4.30 |
| COSCOC2 | 6 | 15 | | NR ⁽²⁾ | 4.30 |
| COSCIB2 | 7 | 14 | 6 (15) (16) (14) (14) <i>MBH341</i> | NR ⁽²⁾ | 2.35 |
| BS | 8 | 13 | (13) (13) (13) (13) (13) (13) (13) (13) | 0.0 | 5.0 |
| n. c. | 9 | 12 | | NR ⁽²⁾ | NR ⁽²⁾ |
| IFOUT | 10 | 11 | (10) (11) MBH337 | 3.85 | 3.85 |
| IFIN1 | 11 | 10 | | 8.36 | 8.36 |
| IFIN2 | 12 | 9 | (1) (10) <i>MBH343</i> | 8.36 | 8.36 |

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| | PIN | | DECODIDEION | AVERAGE D | C VOLTAGE (V) ⁽¹⁾ |
|----------------|---------|---------|--|-------------------|------------------------------|
| SYMBOL | TDA5632 | TDA5633 | DESCRIPTION | BAND A | BAND C |
| V _P | 13 | 8 | supply voltage | 9.0 | 9.0 |
| LOOUT1 | 14 | 7 | | 7.35 | 7.35 |
| LOOUT2 | 15 | 6 | | 7.35 | 7.35 |
| RFGND | 16 | 5 | мвнззв (5) | 0.0 | 0.0 |
| CIN1 | 17 | 4 | | NR ⁽²⁾ | 2.20 |
| CIN2 | 18 | 3 | (17 (4) (3) MBH335 | NR ⁽²⁾ | 2.20 |
| AIN1 | 19 | 2 | | 2.25 | NR ⁽²⁾ |
| AIN2 | 20 | 1 | (19) (2) (1) (1) (1) (1) (1) (1) (1) (1) (1) (1 | 2.25 | NR ⁽²⁾ |

Notes

1. Average DC voltage measured in Fig.10.

2. NR = not relevant.

SOT163-1

9 V VHF and UHF mixers/oscillators for TV and VCR cable tuners

PACKAGE OUTLINES

SO20: plastic small outline package; 20 leads; body width 7.5 mm





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SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

Reflow soldering

Reflow soldering techniques are suitable for all SO and SSOP packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Wave soldering

SO

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

SSOP

Wave soldering is **not** recommended for SSOP packages. This is because of the likelihood of solder bridging due to closely-spaced leads and the possibility of incomplete solder penetration in multi-lead devices. If wave soldering cannot be avoided, the following conditions must be observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow and must incorporate solder thieves at the downstream end.

Even with these conditions, only consider wave soldering SSOP packages that have a body width of 4.4 mm, that is SSOP16 (SOT369-1) or SSOP20 (SOT266-1).

METHOD (SO AND SSOP)

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Repairing soldered joints

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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DEFINITIONS

| Data sheet status | |
|--|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| more of the limiting values m the device at these or at any | accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or hay cause permanent damage to the device. These are stress ratings only and operation of / other conditions above those given in the Characteristics sections of the specification is iting values for extended periods may affect device reliability. |

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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NOTES

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Printed in The Netherlands

537021/50/02/pp20

Date of release: 1996 Aug 16

Document order number: 9397 750 01034

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